



Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

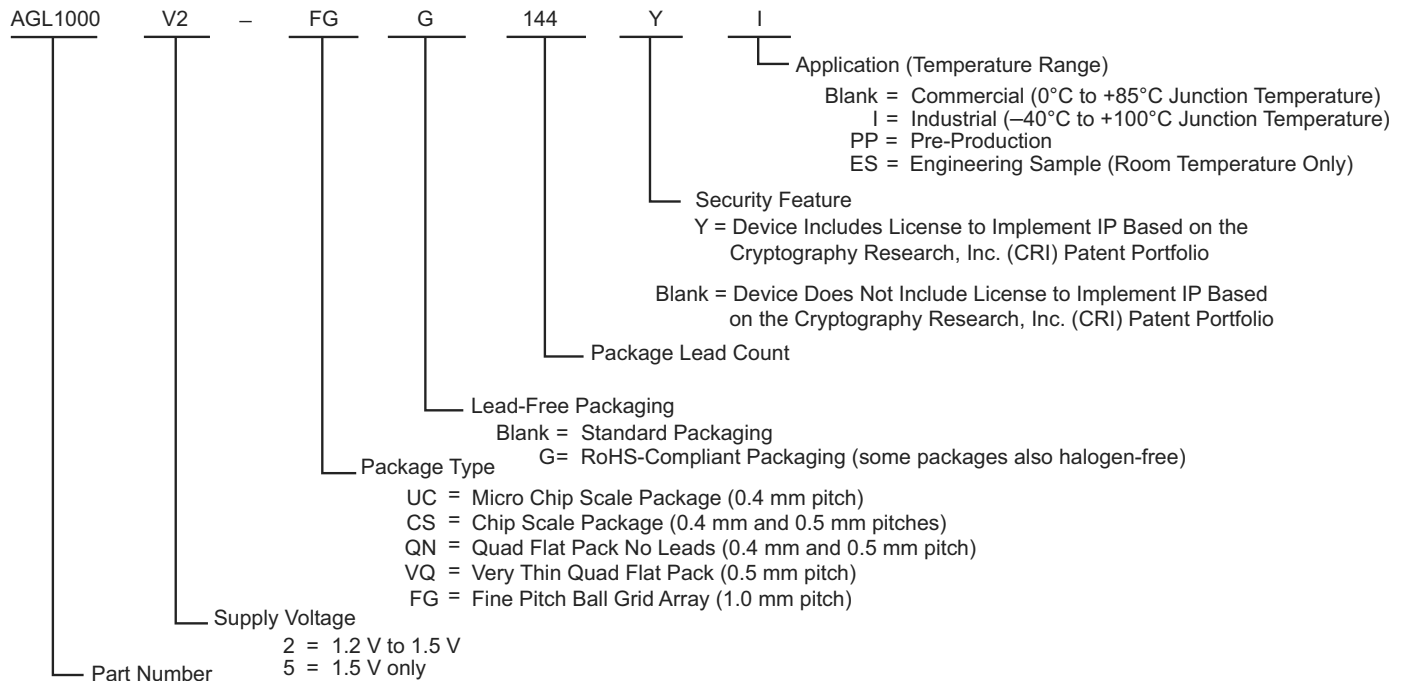
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3072
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agl125v2-vq100t

IGLOO Ordering Information



IGLOO Devices

AGL015 = 15,000 System Gates
 AGL030 = 30,000 System Gates
 AGL060 = 60,000 System Gates
 AGL125 = 125,000 System Gates
 AGL250 = 250,000 System Gates
 AGL400 = 400,000 System Gates
 AGL600 = 600,000 System Gates
 AGL1000 = 1,000,000 System Gates

IGLOO Devices with Cortex-M1

M1AGL250 = 250,000 System Gates
 M1AGL600 = 600,000 System Gates
 M1AGL1000 = 1,000,000 System Gates

Note: Marking Information: IGLOO V2 devices do not have V2 marking, but IGLOO V5 devices are marked accordingly.

field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The IGLOO family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOO family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOO flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOO FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The IGLOO family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOO family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

Advanced Architecture

The proprietary IGLOO architecture provides granularity comparable to standard-cell ASICs. The IGLOO device consists of five distinct and programmable architectural features (Figure 1-1 on page 1-4 and Figure 1-2 on page 1-4):

- Flash*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory[†]
- Extensive CCCs and PLLs[†]
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOO core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC[®] family of third-generation-architecture flash FPGAs.

[†] The AGL015 and AGL030 do not support PLL or SRAM.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-95 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	9	11	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	17	22	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	35	44	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	45	51	10	10
12 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	12	12	91	74	10	10
16 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	16	16	91	74	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-96 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	9	11	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	17	22	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	35	44	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	35	44	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-100 • 1.8 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.25	0.18	1.01	0.66	3.21	3.25	2.33	1.61	6.80	6.85	ns
4 mA	Std.	0.97	2.62	0.18	1.01	0.66	2.68	2.51	2.66	2.46	6.27	6.11	ns
6 mA	Std.	0.97	2.31	0.18	1.01	0.66	2.36	2.15	2.90	2.87	5.95	5.75	ns
8 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.08	2.95	2.98	5.89	5.68	ns
12 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
16 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-101 • 1.8 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	5.78	0.18	1.01	0.66	5.90	5.32	1.95	1.47	9.49	8.91	ns
4 mA	Std.	0.97	4.75	0.18	1.01	0.66	4.85	4.54	2.25	2.21	8.44	8.13	ns
6 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns
8 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-102 • 1.8 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.76	0.18	1.01	0.66	2.79	2.76	1.94	1.51	6.39	6.35	ns
4 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.09	2.24	2.29	5.89	5.69	ns
6 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns
8 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-103 • 1.8 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	5.63	0.18	0.98	0.66	5.74	5.30	1.68	1.24	ns
4 mA	Std.	0.97	4.69	0.18	0.98	0.66	4.79	4.52	1.97	1.98	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-107 • 1.8 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.32	0.26	1.11	1.10	6.43	5.81	2.47	2.16	12.22	11.60	ns
4 mA	Std.	1.55	5.27	0.26	1.11	1.10	5.35	5.01	2.78	2.92	11.14	10.79	ns
6 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns
8 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-108 • 1.8 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.11	1.10	3.26	3.18	2.47	2.20	9.05	8.97	ns
4 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.75	2.50	2.78	3.01	8.54	8.29	ns
6 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns
8 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-109 • 1.8 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	6.13	0.26	1.08	1.10	6.24	5.79	2.08	1.78	ns
4 mA	Std.	1.55	5.17	0.26	1.08	1.10	5.26	4.98	2.38	2.54	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-110 • 1.8 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	3.06	0.26	1.08	1.10	3.10	3.01	2.08	1.83	3.06	ns
4 mA	Std.	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	2.60	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-123 • 1.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.43	0.26	1.27	1.10	6.54	5.95	2.82	2.83	12.32	11.74	ns
4 mA	Std.	1.55	5.59	0.26	1.27	1.10	5.68	5.27	3.07	3.27	11.47	11.05	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-124 • 1.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.02	0.26	1.27	1.10	3.07	2.81	2.82	2.92	8.85	8.59	ns
4 mA	Std.	1.55	2.68	0.26	1.27	1.10	2.72	2.39	3.07	3.37	8.50	8.18	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-125 • 1.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	6.35	0.26	1.22	1.10	6.46	5.93	2.40	2.46	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-126 • 1.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.92	0.26	1.22	1.10	2.96	2.60	2.40	2.56	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) and Multipoint LVDS (M-LVDS) specifications extend the existing LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The drivers require series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus since the driver can be located anywhere on the bus. These configurations can be implemented using the TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 2-14. The input and output buffer delays are available in the LVDS section in Table 2-149 on page 2-81 and Table 2-150 on page 2-81.

Example: For a bus consisting of 20 equidistant loads, the following terminations provide the required differential voltage, in worst-case Industrial operating conditions, at the farthest receiver: $R_S = 60\ \Omega$ and $R_T = 70\ \Omega$, given $Z_0 = 50\ \Omega$ (2") and $Z_{stub} = 50\ \Omega$ (~1.5").

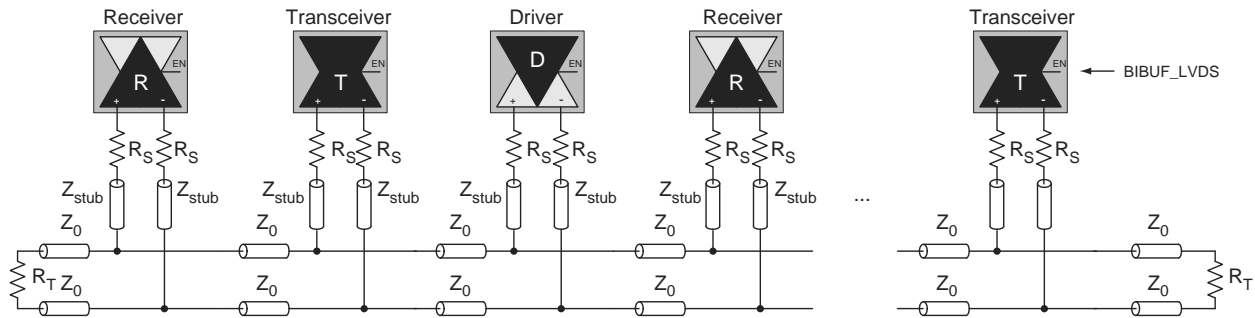


Figure 2-14 • B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers

LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-15. The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.

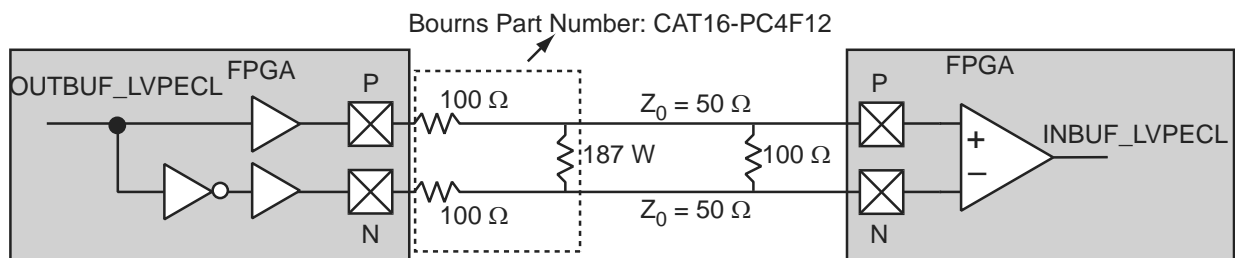


Figure 2-15 • LVPECL Circuit Diagram and Board-Level Implementation

Table 2-156 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t _{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t _{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t _{OHD}	Data Hold Time for the Output Data Register	FF, HH
t _{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t _{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t _{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
t _{OREMCLR}	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
t _{ORECCLR}	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t _{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t _{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t _{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t _{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t _{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
t _{OECLR2Q}	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
t _{OEREMCLR}	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
t _{OERECCLR}	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t _{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t _{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t _{IHD}	Data Hold Time for the Input Data Register	CC, AA
t _{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t _{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t _{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
t _{IREMCLR}	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
t _{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-17 on page 2-86 for more information.

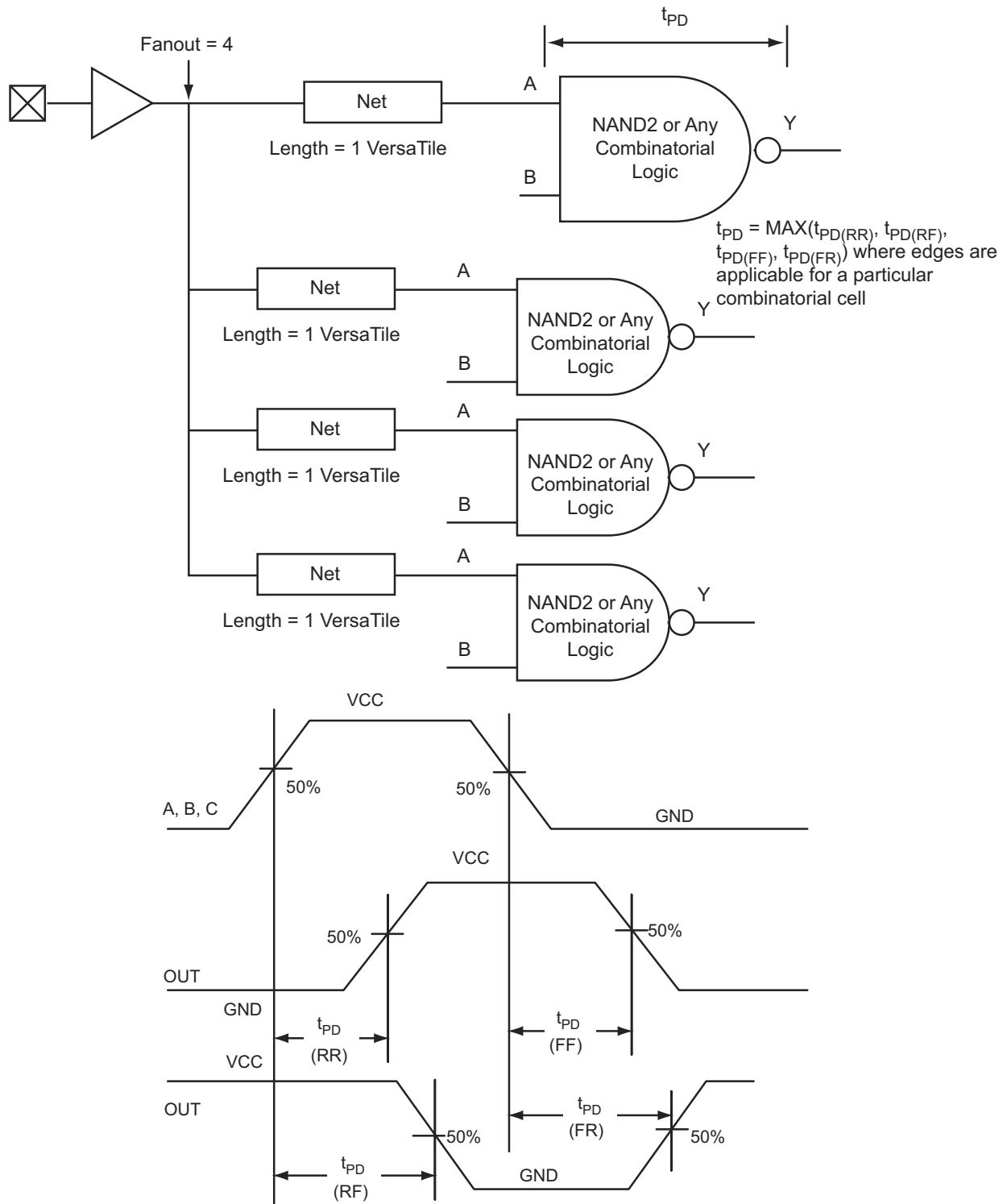


Figure 2-26 • Timing Model and Waveforms

1.2 V DC Core Voltage**Table 2-172 • Register Delays****Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	1.61	ns
t_{SUD}	Data Setup Time for the Core Register	1.17	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	1.29	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.87	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.89	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.24	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.46	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.46	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.95	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Embedded SRAM and FIFO Characteristics

SRAM

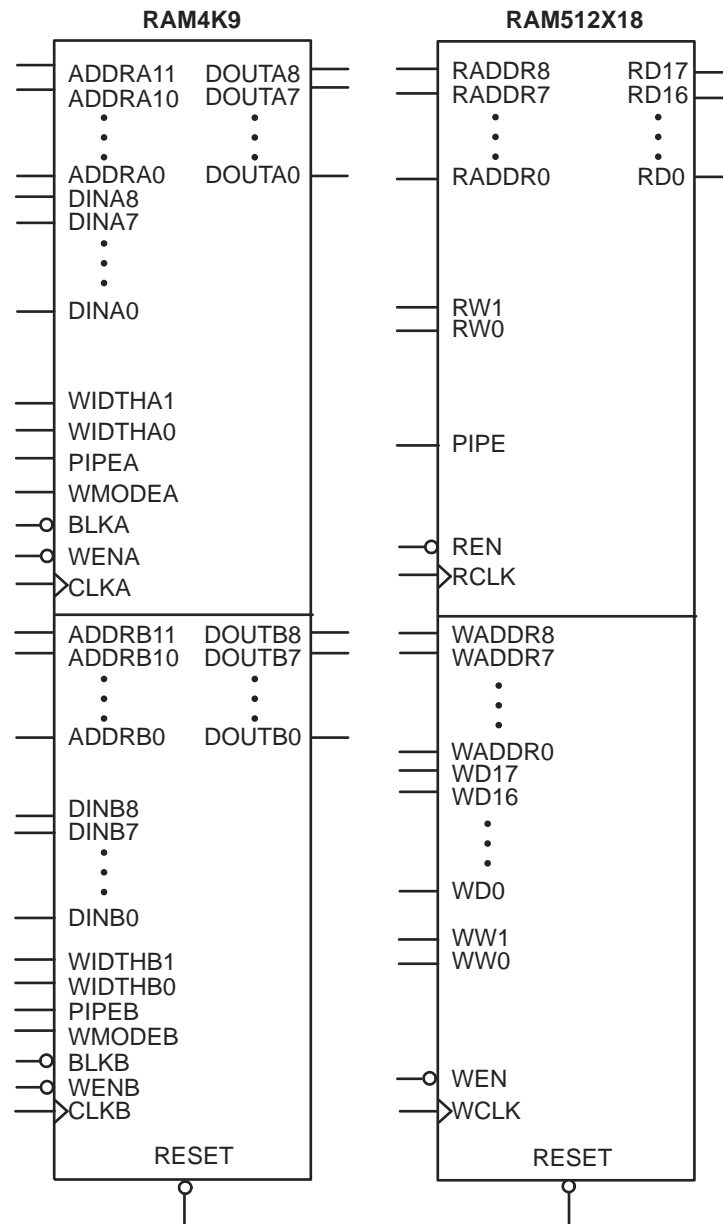


Figure 2-31 • RAM Models

Timing Waveforms

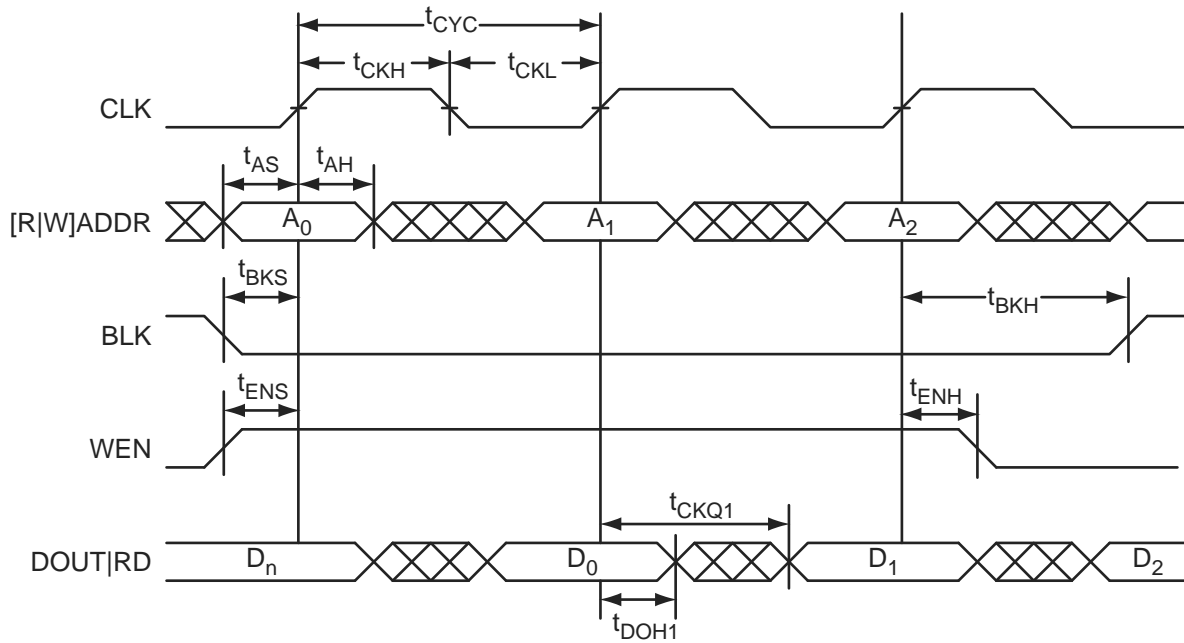


Figure 2-32 • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.

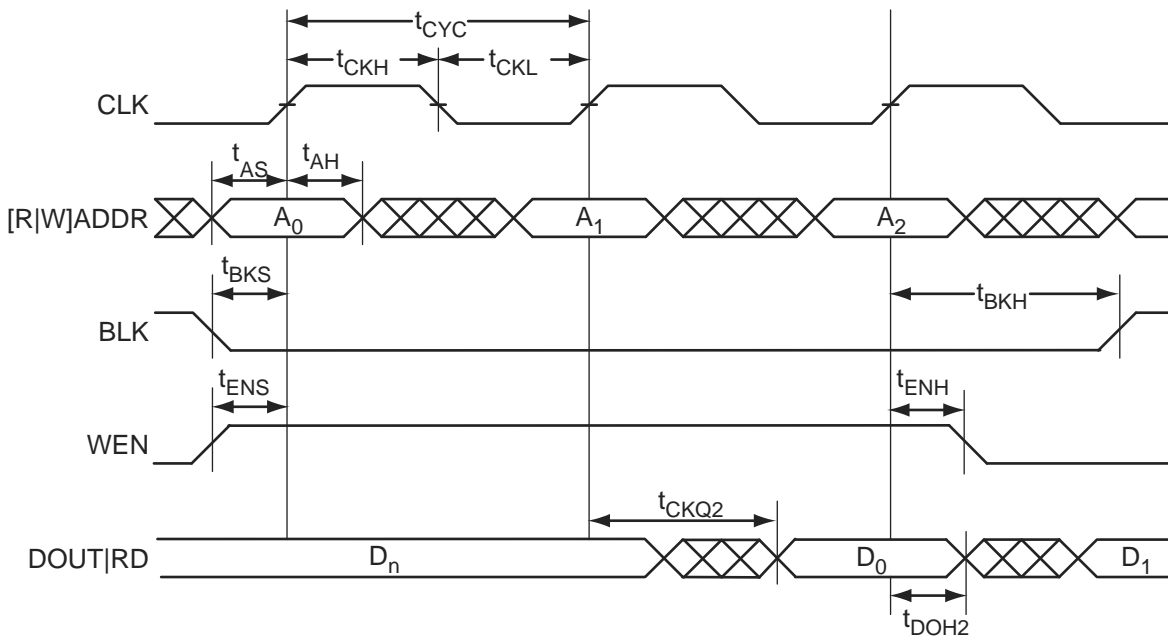


Figure 2-33 • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-191 • RAM4K9

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.81	ns
t_{ENH}	REN, WEN hold time	0.16	ns
t_{BKS}	BLK setup time	1.65	ns
t_{BKH}	BLK hold time	0.16	ns
t_{DS}	Input data (DIN) setup time	0.71	ns
t_{DH}	Input data (DIN) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	3.53	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	3.06	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	1.81	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.23	ns
t_{C2CRWL}^1	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.35	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	0.41	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	2.06	ns
	RESET Low to data out Low on DOUT (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-192 • RAM512X18**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.73	ns
t_{ENH}	REN, WEN hold time	0.08	ns
t_{DS}	Input data (WD) setup time	0.71	ns
t_{DH}	Input data (WD) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	4.21	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.71	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address - Applicable to Opening Edge	0.35	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address - Applicable to Opening Edge	0.42	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	2.06	ns
	RESET Low to data out Low on RD (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

QN132	
Pin Number	AGL125 Function
A1	GAB2/IO69RSB1
A2	IO130RSB1
A3	VCCIB1
A4	GFC1/IO126RSB1
A5	GFB0/IO123RSB1
A6	VCCPLF
A7	GFA1/IO121RSB1
A8	GFC2/IO118RSB1
A9	IO115RSB1
A10	VCC
A11	GEB1/IO110RSB1
A12	GEA0/IO107RSB1
A13	GEC2/IO104RSB1
A14	IO100RSB1
A15	VCC
A16	IO99RSB1
A17	IO96RSB1
A18	IO94RSB1
A19	IO91RSB1
A20	IO85RSB1
A21	IO79RSB1
A22	VCC
A23	GDB2/IO71RSB1
A24	TDI
A25	TRST
A26	GDC1/IO61RSB0
A27	VCC
A28	IO60RSB0
A29	GCC2/IO59RSB0
A30	GCA2/IO57RSB0
A31	GCA0/IO56RSB0
A32	GCB1/IO53RSB0
A33	IO49RSB0
A34	VCC
A35	IO44RSB0
A36	GBA2/IO41RSB0

QN132	
Pin Number	AGL125 Function
A37	GBB1/IO38RSB0
A38	GBC0/IO35RSB0
A39	VCCIB0
A40	IO28RSB0
A41	IO22RSB0
A42	IO18RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	IO07RSB0
A46	VCC
A47	GAC1/IO05RSB0
A48	GAB0/IO02RSB0
B1	IO68RSB1
B2	GAC2/IO131RSB1
B3	GND
B4	GFC0/IO125RSB1
B5	VCOMPLF
B6	GND
B7	GFB2/IO119RSB1
B8	IO116RSB1
B9	GND
B10	GEB0/IO109RSB1
B11	VMV1
B12	FF/GEB2/IO105RSB1
B13	IO101RSB1
B14	GND
B15	IO98RSB1
B16	IO95RSB1
B17	GND
B18	IO87RSB1
B19	IO81RSB1
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO62RSB0

QN132	
Pin Number	AGL125 Function
B25	GND
B26	NC
B27	GCB2/IO58RSB0
B28	GND
B29	GCB0/IO54RSB0
B30	GCC1/IO51RSB0
B31	GND
B32	GBB2/IO43RSB0
B33	VMV0
B34	GBA0/IO39RSB0
B35	GBC1/IO36RSB0
B36	GND
B37	IO26RSB0
B38	IO21RSB0
B39	GND
B40	IO13RSB0
B41	IO08RSB0
B42	GND
B43	GAC0/IO04RSB0
B44	GNDQ
C1	GAA2/IO67RSB1
C2	IO132RSB1
C3	VCC
C4	GFB1/IO124RSB1
C5	GFA0/IO122RSB1
C6	GFA2/IO120RSB1
C7	IO117RSB1
C8	VCCIB1
C9	GEA1/IO108RSB1
C10	GNDQ
C11	GEA2/IO106RSB1
C12	IO103RSB1
C13	VCCIB1
C14	IO97RSB1
C15	IO93RSB1
C16	IO89RSB1

FG256	
Pin Number	AGL400 Function
H3	GFB1/IO146PPB3
H4	VCOMPLF
H5	GFC0/IO147NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO67NPB1
H13	GCB1/IO68PPB1
H14	GCA0/IO69NPB1
H15	NC
H16	GCB0/IO68NPB1
J1	GFA2/IO144PPB3
J2	GFA1/IO145PDB3
J3	VCCPLF
J4	IO143NDB3
J5	GFB2/IO143PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO71PPB1
J13	GCA1/IO69PPB1
J14	GCC2/IO72PPB1
J15	NC
J16	GCA2/IO70PDB1
K1	GFC2/IO142PDB3
K2	IO144NPB3
K3	IO141PPB3
K4	IO120RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	AGL400 Function
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO71NPB1
K14	IO74RSB1
K15	IO72NPB1
K16	IO70NDB1
L1	IO142NDB3
L2	IO141NPB3
L3	IO125RSB2
L4	IO139RSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO78VPB1
L14	IO76VDB1
L15	IO76UDB1
L16	IO75PDB1
M1	IO140PDB3
M2	IO130RSB2
M3	IO138NPB3
M4	GEC0/IO137NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO108RSB2
M9	IO101RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO83RSB2
M14	GDB1/IO78UPB1

FG256	
Pin Number	AGL400 Function
M15	GDC1/IO77UDB1
M16	IO75NDB1
N1	IO140NDB3
N2	IO138PPB3
N3	GEC1/IO137PPB3
N4	IO131RSB2
N5	GNDQ
N6	GEA2/IO134RSB2
N7	IO117RSB2
N8	IO111RSB2
N9	IO99RSB2
N10	IO94RSB2
N11	IO87RSB2
N12	GNDQ
N13	IO93RSB2
N14	VJTAG
N15	GDC0/IO77VDB1
N16	GDA1/IO79UDB1
P1	GEB1/IO136PDB3
P2	GEB0/IO136NDB3
P3	VMV2
P4	IO129RSB2
P5	IO128RSB2
P6	IO122RSB2
P7	IO115RSB2
P8	IO110RSB2
P9	IO98RSB2
P10	IO95RSB2
P11	IO88RSB2
P12	IO84RSB2
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO79VDB1
R1	GEA1/IO135PDB3
R2	GEA0/IO135NDB3
R3	IO127RSB2
R4	GEC2/IO132RSB2

FG256	
Pin Number	AGL400 Function
R5	IO123RSB2
R6	IO118RSB2
R7	IO112RSB2
R8	IO106RSB2
R9	IO100RSB2
R10	IO96RSB2
R11	IO89RSB2
R12	IO85RSB2
R13	GDB2/IO81RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO126RSB2
T3	FF/GEB2/IO133RSB2
T4	IO124RSB2
T5	IO116RSB2
T6	IO113RSB2
T7	IO107RSB2
T8	IO105RSB2
T9	IO102RSB2
T10	IO97RSB2
T11	IO92RSB2
T12	GDC2/IO82RSB2
T13	IO86RSB2
T14	GDA2/IO80RSB2
T15	TMS
T16	GND

FG256	
Pin Number	AGL600 Function
H3	GFB1/IO163PPB3
H4	VCOMPLF
H5	GFC0/IO164NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO69NPB1
H13	GCB1/IO70PPB1
H14	GCA0/IO71NPB1
H15	IO67NPB1
H16	GCB0/IO70NPB1
J1	GFA2/IO161PPB3
J2	GFA1/IO162PDB3
J3	VCCPLF
J4	IO160NDB3
J5	GFB2/IO160PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO73PPB1
J13	GCA1/IO71PPB1
J14	GCC2/IO74PPB1
J15	IO80PPB1
J16	GCA2/IO72PDB1
K1	GFC2/IO159PDB3
K2	IO161NPB3
K3	IO156PPB3
K4	IO129RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	AGL600 Function
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO73NPB1
K14	IO80NPB1
K15	IO74NPB1
K16	IO72NDB1
L1	IO159NDB3
L2	IO156NPB3
L3	IO151PPB3
L4	IO158PSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO87NPB1
L14	IO85NDB1
L15	IO85PDB1
L16	IO84PDB1
M1	IO150PDB3
M2	IO151NPB3
M3	IO147NPB3
M4	GEC0/IO146NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO117RSB2
M9	IO110RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO94RSB2
M14	GDB1/IO87PPB1

FG256	
Pin Number	AGL600 Function
M15	GDC1/IO86PDB1
M16	IO84NDB1
N1	IO150NDB3
N2	IO147PPB3
N3	GEC1/IO146PPB3
N4	IO140RSB2
N5	GNDQ
N6	GEA2/IO143RSB2
N7	IO126RSB2
N8	IO120RSB2
N9	IO108RSB2
N10	IO103RSB2
N11	IO99RSB2
N12	GNDQ
N13	IO92RSB2
N14	VJTAG
N15	GDC0/IO86NDB1
N16	GDA1/IO88PDB1
P1	GEB1/IO145PDB3
P2	GEB0/IO145NDB3
P3	VMV2
P4	IO138RSB2
P5	IO136RSB2
P6	IO131RSB2
P7	IO124RSB2
P8	IO119RSB2
P9	IO107RSB2
P10	IO104RSB2
P11	IO97RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO88NDB1
R1	GEA1/IO144PDB3
R2	GEA0/IO144NDB3
R3	IO139RSB2
R4	GEC2/IO141RSB2

FG484	
Pin Number	AGL600 Function
C21	NC
C22	VCCIB1
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0
D7	GAB0/IO02RSB0
D8	IO11RSB0
D9	IO16RSB0
D10	IO18RSB0
D11	IO28RSB0
D12	IO34RSB0
D13	IO37RSB0
D14	IO41RSB0
D15	IO43RSB0
D16	GBB1/IO57RSB0
D17	GBA0/IO58RSB0
D18	GBA1/IO59RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO173PDB3
E5	GAA2/IO174PDB3
E6	GNDQ
E7	GAB1/IO03RSB0
E8	IO13RSB0
E9	IO14RSB0
E10	IO21RSB0
E11	IO27RSB0
E12	IO32RSB0

Revision / Version	Changes	Page
Revision 8 (cont'd)	Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, Table 2-14 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, Table 2-15 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, and Table 2-16 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings ¹ were updated to change PDC2 to PDC6 and PDC3 to PDC7. The table notes were updated to reflect that power was measured on VCCI.	2-10 through 2-11
	In Table 2-19 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices, the description for PAC13 was changed from Static to Dynamic.	2-13
	Table 2-20 • Different Components Contributing to the Static Power Consumption in IGLOO Devices and Table 2-22 • Different Components Contributing to the Static Power Consumption in IGLOO Device were updated to add PDC6 and PDC7, and to change the definition for PDC5 to bank quiescent power. Subtitles were added to indicate type of devices and core supply voltage.	2-14, 2-16
	The "Total Static Power Consumption—PSTAT" section was updated to revise the calculation of P _{STAT} , including PDC6 and PDC7.	2-17
	Footnote † was updated to include information about PAC13. The PLL Contribution equation was changed from: $P_{PLL} = P_{AC13} + P_{AC14} * F_{CLKOUT}$ to $P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$.	2-18
Revision 7 (Jun 2008) Packaging v1.5	The "QN132" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-28
Revision 6 (Jun 2008) Packaging v1.4	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	Pin numbers were added to the "QN68" package diagram. Note 2 was added below the diagram.	4-25
Revision 5 (Mar 2008) Packaging v1.3	The "CS196" package and pin table was added for AGL250.	4-12
Revision 4 (Mar 2008) Product Brief v1.0	The "Low Power" section was updated to change "1.2 V and 1.5 V Core Voltage" to "1.2 V and 1.5 V Core and I/O Voltage." The text "(from 12 μW)" was removed from "Low Power Active FPGA Operation."	I
	1.2_V was added to the list of core and I/O voltages in the "Advanced I/O" and "I/Os with Advanced I/O Standards" section sections.	I, 1-7
	The "Embedded Memory" section was updated to remove the footnote reference from the section heading and place it instead after "4,608-Bit" and "True Dual-Port SRAM (except x18)."	I